



EPC2010C Information

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For Reference Only

Part Number EPC2010C

Manufacturer EPC

Category Discrete Semiconductor Products

Transistors - FETs, MOSFETs - Single

Description TRANS GAN 200V 22A BUMPED DIE

Package Die

For the pricing/inventory/lead time, please contact

us

Website: https://www.heisener.com E-mail: salesdept@heisener.com



Request a Quote

Certified Quality

Heisener's commitment to quality has shaped our processes for sourcing, testing, shipping, and every step in between. This foundation underlies each component we sell.









EPC2010C Specifications

Manufacturer Part Number	EPC2010C
Manufacturer	EPC
Category	Discrete Semiconductor Products
	Transistors - FETs, MOSFETs - Single
Package	Die
Series	eGaN?
FET Type	N-Channel
Technology	GaNFET (Gallium Nitride)
Drain to Source Voltage (Vdss)	200V
Current - Continuous Drain (Id) @ 25°C	22A (Ta)
Drive Voltage (Max Rds On, Min Rds On)	5V
Vgs(th) (Max) @ Id	2.5V @ 3mA
Gate Charge (Qg) (Max) @ Vgs	5.3nC @ 5V
Input Capacitance (Ciss) (Max) @ Vds	540pF @ 100V
Vgs (Max)	+6V, -4V
FET Feature	-
Power Dissipation (Max)	-
Rds On (Max) @ Id, Vgs	25 mOhm @ 12A, 5V
Operating Temperature	-40°C ~ 150°C (TJ)
Mounting Type	Surface Mount
Supplier Device Package	Die Outline (7-Solder Bar)
Package / Case	Die
	Report errors?

EPC2010C Guarantees



Quality Guarantees

We provide 90 days warranty. *

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



Service Guarantees

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

EPC2010C Payment Methods





















EPC2010C Shipping Methods













If you have any question about EPC2010C, please do not hesitate to contact us!

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